

Fig. 1

(59) SEMICONDUCTOR DEVICE

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PURPOSE: To remove defective factors, such as H_2 , H_2O , etc. having an adverse effect on a semiconductor device by incorporating an adsorbent into the cavity of a semiconductor package.

CONSTITUTION: A metallized layer 7 consisting of an Mg group alloy as a hydrogen adsorbent is formed on the back, the cavity side, of a cap 1 for a cerdip type semiconductor package, and a porous alumina layer 8 as a moisture adsorbent is formed to one part on the surface of the metallized layer 7. It is desirable that the Mg group alloy, such as an alloy consisting of Mg and Ni, an alloy consisting of Mg and Cu or the like is used as the hydrogen adsorbent employed. An alloy or a metal adsorbing hydrogen, such as a Pd metal, an LaCo alloy or the like may be used as other metals or alloys.

